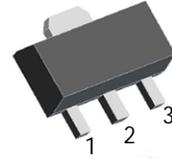




**A94** TRANSISTOR (PNP)

SOT-89



- 1. BASE
- 2. COLLECTOR
- 3. EMITTER

**FEATURES**  
High voltage

**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-400	V
$V_{CEO}$	Collector-Emitter Voltage	-400	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-0.2	A
$I_{CM}$	Collector Current- Pulsed	-0.3	A
$P_C$	Collector Power Dissipation	0.5	W
$T_J$	Junction Temperature	150	°C
$T_{stg}$	storage Temperature	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -400V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -400V, I_B = 0$			-5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -10mA$	80		300	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	70			
	$h_{FE(3)}$	$V_{CE} = -10V, I_C = -100mA$	60			
	$h_{FE(4)}$	$V_{CE} = -10V, I_C = -50mA$	80			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.2	V
	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.75	V
Transition frequency	$f_T$	$V_{CE} = -20V, I_C = -10mA$ $f = 30MHz$	50			MHz

# Typical Characteristics

